**PN3563** 



## **NPN RF Amplifier**

FAIRCHILD

This device is designed for use as RF amplifiers, oscillators and multipliers with collector currents in the 1.0 mA to 30 mA range. Sourced from Process 43. See PN918 for characteristics.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	15	V
V <sub>CBO</sub>	Collector-Base Voltage	30	V
V <sub>EBO</sub>	Emitter-Base Voltage	2.0	V
Ic	Collector Current - Continuous	50	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### NOTES:

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1) These ratings are based on a maximum junction temperature of 150 degrees C. 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Thermal Characteristics TA = 25°C unless otherwise noted

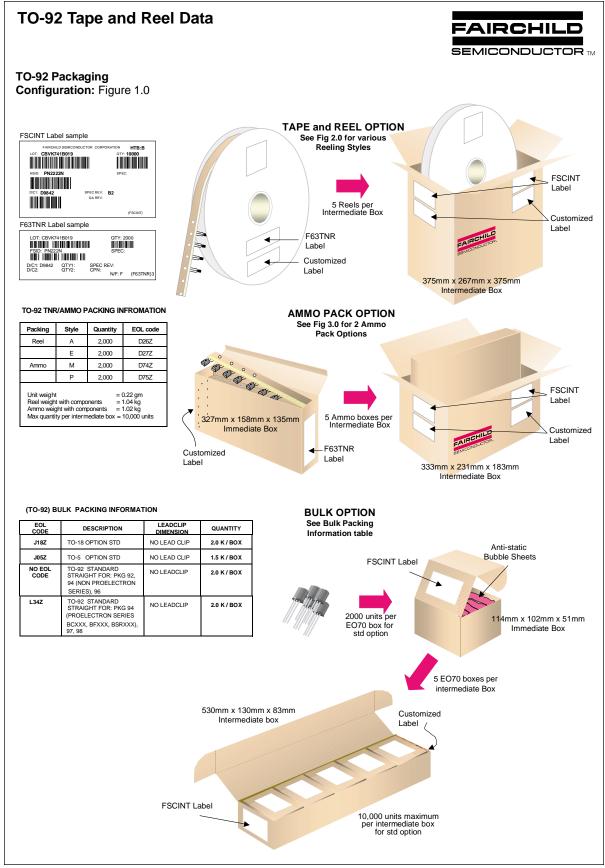
Symbol	Characteristic	Мах	Units
		PN3563	
P <sub>D</sub>	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case	125	°C/W
$R_{\theta J A}$	Thermal Resistance, Junction to Ambient	357	°C/W

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# NPN RF Amplifier (continued)

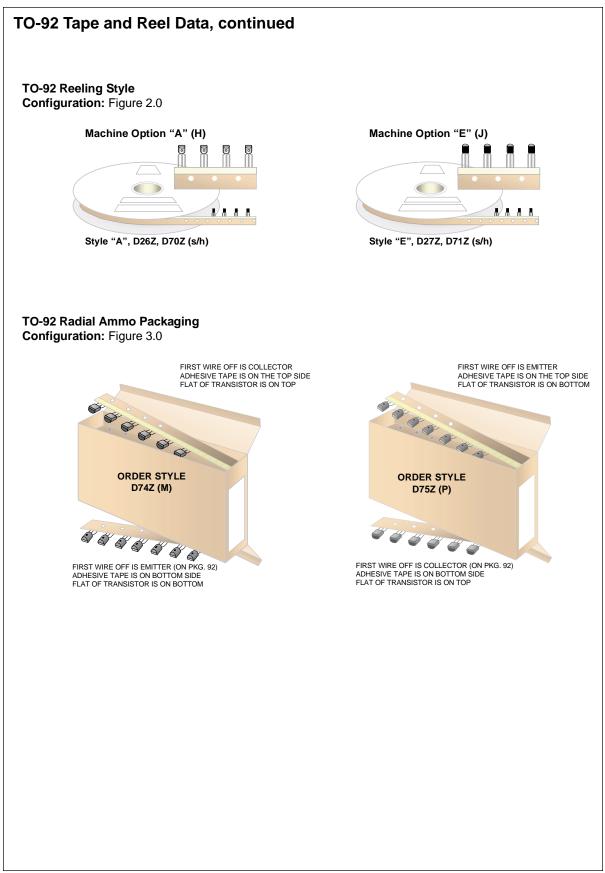
V <sub>(BR)EBO</sub> Emitter-Base Breakdown Vo	/oltage $I_{c} = 100 \mu\text{A}, I_{E} = 0$	15		
V <sub>CEO(sus)</sub> Collector-Emitter Sustaining           V <sub>(BR)CBO</sub> Collector-Base Breakdown V           V <sub>(BR)EBO</sub> Emitter-Base Breakdown V	/oltage $I_{c} = 100 \mu\text{A}, I_{E} = 0$	15		
V <sub>(BR)CBO</sub> Collector-Base Breakdown V V <sub>(BR)EBO</sub> Emitter-Base Breakdown V	/oltage $I_{c} = 100 \mu\text{A}, I_{E} = 0$			V
V <sub>(BR)EBO</sub> Emitter-Base Breakdown Vo		30		v
(	bltage $I_E = 10 \mu\text{A}, I_C = 0$	2.0		V
	$V_{CB} = 15 \text{ V}, I_E = 0$ $V_{CB} = 15 \text{ V}, T_A = 150^{\circ}\text{C}$	-	0.05 5.0	μA nA
ON CHARACTERISTICS*			0.0	10 (
DFE DC Current Gain	$I_{C} = 8.0 \text{ mA}, V_{CE} = 10 \text{ V}$	20	200	
SMALL SIGNAL CHARACTERIST		600	1500	MHz
	f = 100 MHz			
Cobo Output Capacitance	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1.0 MH V <sub>CB</sub> = 0, I <sub>E</sub> = 0, f = 1.0 MHz	Z	1.7 3.0	pF pF
Cibo Input Capacitance	$V_{CB} = 0, T_E = 0, T = 1.0 \text{ MHz}$ $V_{BE} = 0.5 \text{ V}, \text{ I}_{C} = 0, \text{ f} = 140 \text{ MHz}$	łz	2.0	pr pF
n <sub>fe</sub> Small-Signal Current Gain	I <sub>C</sub> = 8.0 mA, V <sub>CE</sub> = 10 V, f = 1.0 MHz	20	250	
rb'C <sub>C</sub> Collector Base Time Cons		8.0	25	pS
FUNCTIONAL TEST G <sub>pe</sub> Amplifier Power Gain	$I_{c} = 8.0 \text{ mA}, V_{CB} = 10 \text{ V},$ f = 200 MHz	14	26	dB
	$I_{C} = 8.0 \text{ mA}, V_{CB} = 10 \text{ V},$ f = 200 MHz	14	26	dB

PN3563

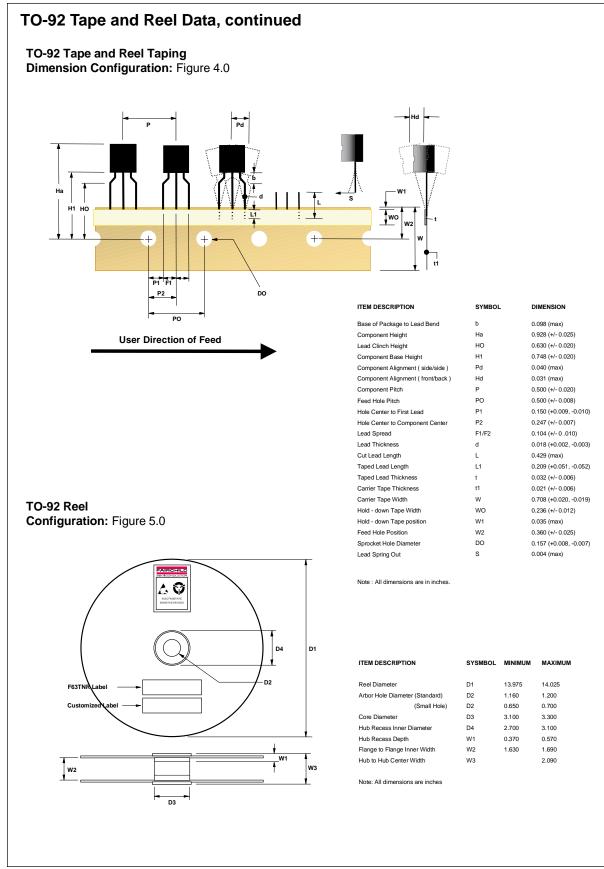


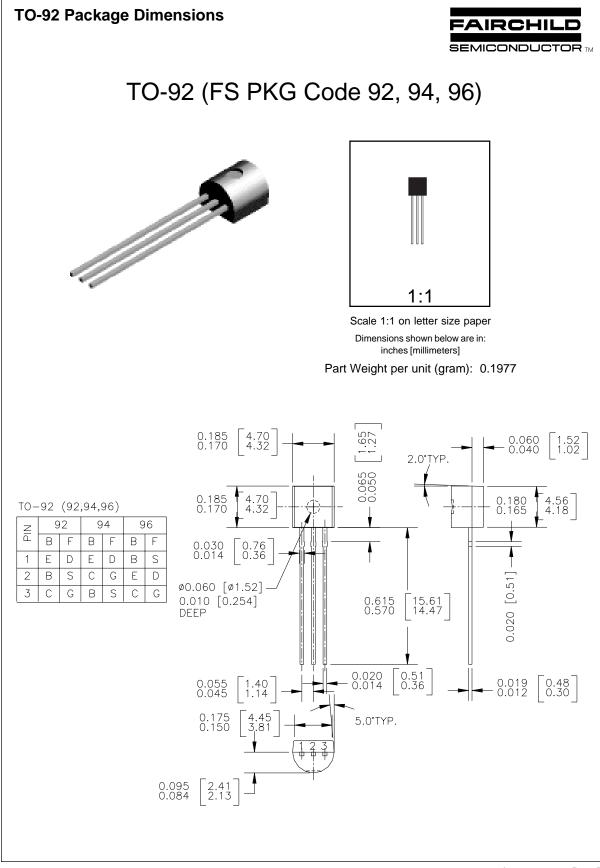
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